

ABSTRACT OF THE DISCLOSURE

A semiconductor light-receiving device includes:  
a semi-insulating substrate; a semiconductor layer of a  
first conduction type that is formed on the semi-  
5 insulating substrate; a buffer layer of the first  
conduction type that is formed on the semi-insulating  
substrate and has a lower impurity concentration than  
the semiconductor layer of the first conduction type; a  
light absorption layer that is formed on the buffer  
10 layer and generates carriers in accordance with  
incident light; a semiconductor layer of a second  
conduction type that is formed on the light absorption  
layer; and a semiconductor intermediate layer that is  
interposed between the buffer layer and the light  
15 absorption layer, and has a forbidden bandwidth within  
a range lying between the forbidden bandwidth of the  
buffer layer and the forbidden bandwidth of the light  
absorption layer.

20